# Abstracts

## High-Frequency Large-Signal Physical Modeling of Microwave Semiconductor Devices

*M.A. Alsunaidi and S.M. El-Ghazaly. "High-Frequency Large-Signal Physical Modeling of Microwave Semiconductor Devices." 1995 MTT-S International Microwave Symposium Digest 95.2 (1995 Vol. II [MWSYM]): 619-622.*

High frequency characterization of microwave semiconductor devices is presented based on physical modeling. The active device is simulated using a fast and accurate model based on the hydrodynamic equations which simulate the behavior of short gate field-effect transistors (FETs). The device response is analyzed as a function of tie input signal frequency and its amplitude.

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